AMENDMENT TO THE CLAIMS

1. (Currently Amended) A semiconductor apparatus comprising:

a semiconductor chip including a power semiconductor device constructed by using a wide band gap semiconductor;

a first base material made of an electrically conductive material and electrically connected to a part of a lower surface of said semiconductor chip;

a heat conducting member coming in contact with a part of an upper surface of said semiconductor chip and releasing heat directly from said semiconductor chip; and

an encapsulating material for encapsulating said semiconductor chip and said heat conducting member,

wherein the semiconductor apparatus further comprises a second base material made of a metal material and connected to a part of said upper surface of said semiconductor chip,

wherein said power semiconductor device is a vertical element,

wherein a part of said first base material is extruded outside said encapsulating material and works as [[an]] a first external connection terminal,

wherein a part of said second base material is extruded outside said encapsulating material and works as a second external connection terminal,

wherein a first intermediate member made of an electrically conductive material and a second intermediate member made of a material having lower heat conductivity than said first intermediate member are provided between said first base material and said semiconductor chip, and

wherein the semiconductor chip and the first base material are electrically connected with each other through the first intermediate member.

2. (Original) The semiconductor apparatus of Claim 1,

wherein said power semiconductor device has a region where a current passes at a current density of 50 A/cm^2 or more.

3. (Original) The semiconductor apparatus of Claim 1 or 2,

wherein said encapsulating material is made of a resin or glass, and

said heat conducting member is exposed from said encapsulating material.

4. (Original) The semiconductor apparatus of Claim 3, further comprising a radiation fin that is in contact with said heat conducting member and is extruded outside said encapsulating material.

5. (Withdrawn) The semiconductor apparatus of Claim 1 or 2, further comprising a film for covering said encapsulating material.

6. (Withdrawn) The semiconductor apparatus of Claim 5, further comprising a radiation fin opposing said heat conducting member with said film sandwiched therebetween.

7-11. (Cancelled)

12. (Withdrawn) A semiconductor apparatus comprising:

a semiconductor chip including a power semiconductor device constructed by using a wide band gap semiconductor;

a base material made of an electrically conductive material and connected to a part of a face of said semiconductor chip;

a heat conducting member in contact with a part of the face of said semiconductor chip;

a vessel in contact with said heat conducting member and encapsulating said semiconductor chip, said base material and said heat conducting member; and

an external connection terminal electrically connected to said base material and extruded from said vessel.

13. (Withdrawn) The semiconductor apparatus of Claim 12,

wherein a region around said semiconductor chip, said base material and said heat conducting member within said vessel is filled with glass, a resin, an inert gas or a gas reduced in pressure.

14. (Withdrawn) The semiconductor apparatus of Claim 12 or 13, further comprising a radiation fin opposing said heat conducting member with a part of said vessel sandwiched therebetween.

15. (Previously presented) The semiconductor apparatus of claim 1,

wherein another heat conducting member is in direct contact with the lower surface of said semiconductor chip.

16. (Currently amended) The semiconductor apparatus of claim 1,

wherein a contact area between said semiconductor chip and said first base material is smaller than a half of an area of the upper or lower surface of said semiconductor chip.

17. (Currently amended) The semiconductor apparatus of claim 1,

~~wherein said power semiconductor device is a vertical element, and~~

~~said semiconductor apparatus~~ further ~~comprises~~ comprising another semiconductor chip that is stacked on said semiconductor chip and a part of which is connected to said first base material.

18. (Currently amended) The semiconductor apparatus of claim 1,

wherein said first external connection terminal of said first base material is constructed to be mounted on a print wiring board.

19. (Previously Presented) The semiconductor apparatus of claim 1,

wherein said wide band gap semiconductor is SiC.